P-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	-60 V
I_D	-0.26 A
$R_{DS(ON)}$(at V_{GS}=-10V)	3
$R_{DS(ON)}$(at V_{GS}=-4.5V)	3.5

Gate-Source ESD Rating Up to 2KV (HBM)

Typical Electrical and Thermal Characteristics Diagrams

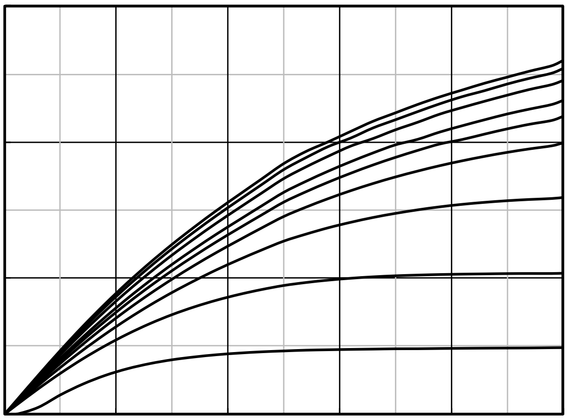


Figure 1. Output Characteristics

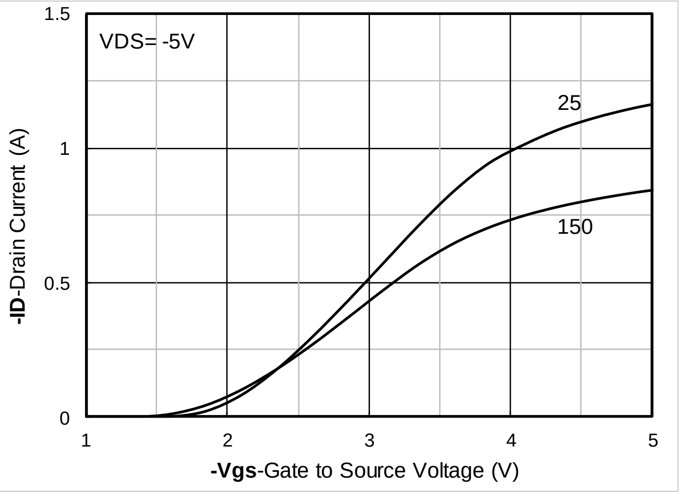


Figure 2. Transfer Characteristics

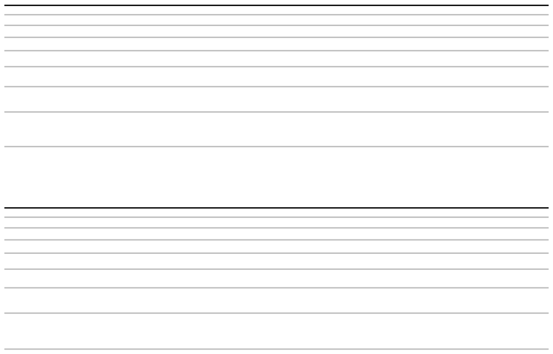


Figure 3. Capacitance Characteristics

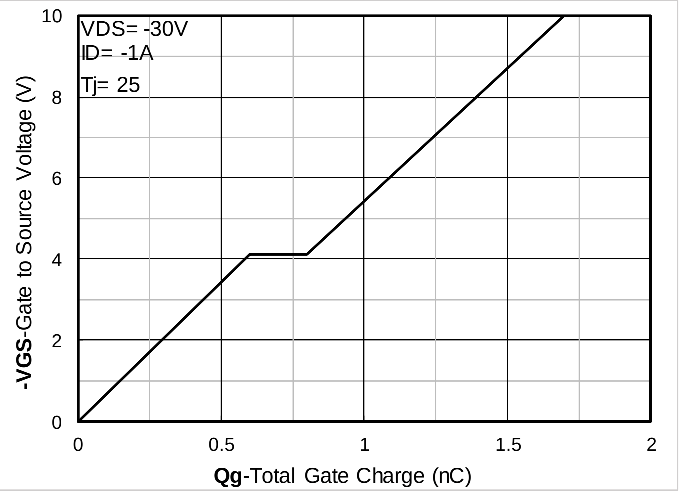


Figure 4. Gate Charge

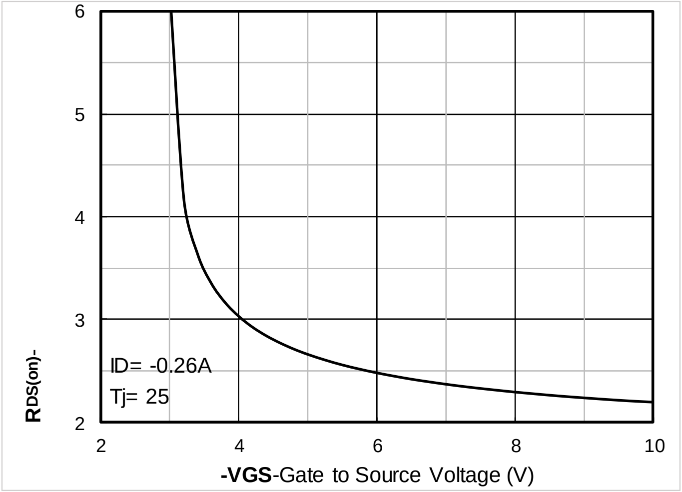


Figure 5. On-Resistance vs Gate to Source Voltage

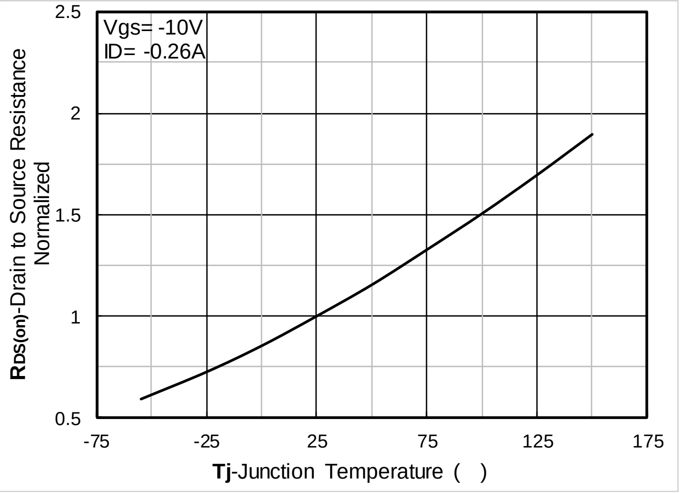


Figure 6. Normalized On-Resistance

Figure 13. Maximum Transient Thermal Impedance

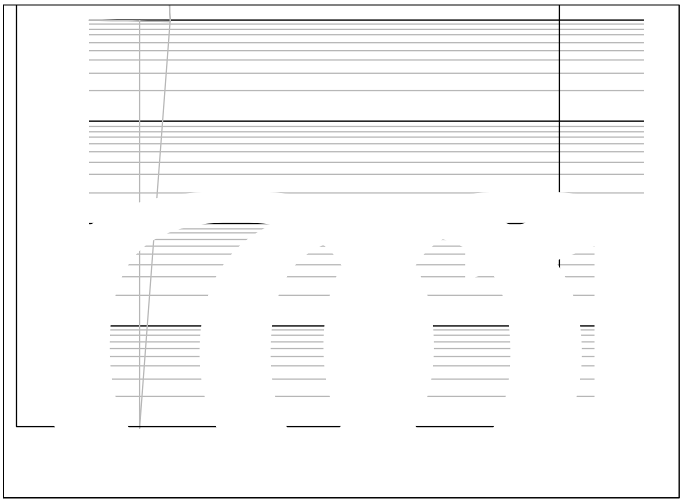
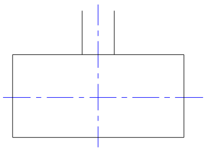
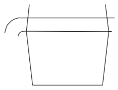
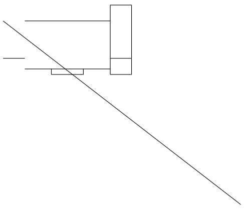


Figure 14. Safe Operation Area

SOT-523 Package information







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